

# 2SC5037, 2SC5037A

Silicon NPN triple diffusion planar type

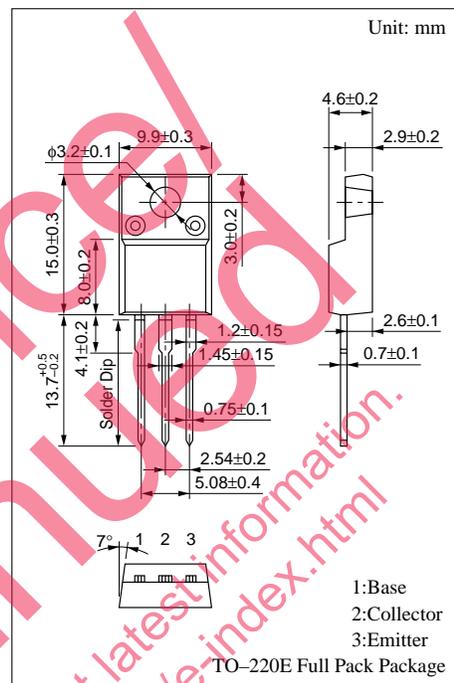
For high breakdown voltage high-speed switching

## Features

- High-speed switching
- High collector to base voltage  $V_{CBO}$
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- Full-pack package with outstanding insulation, which can be installed to the heat sink with one screw

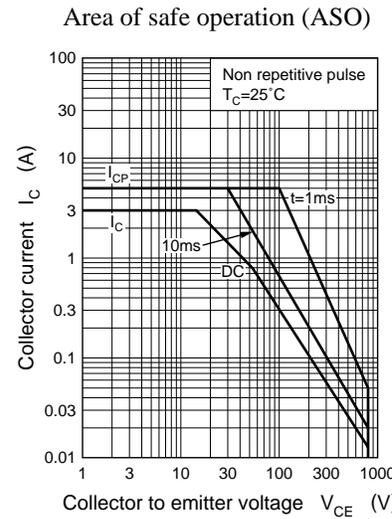
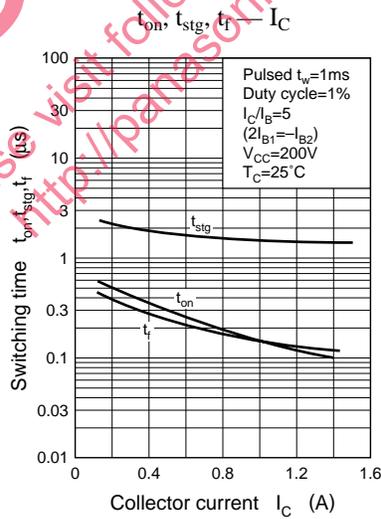
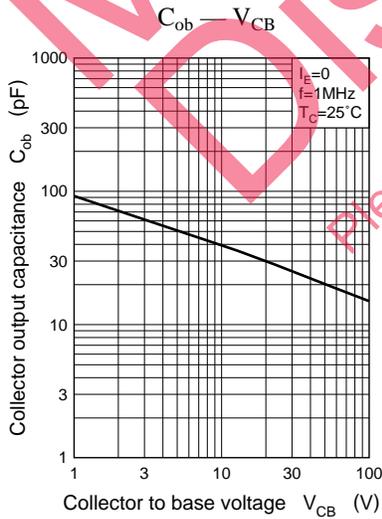
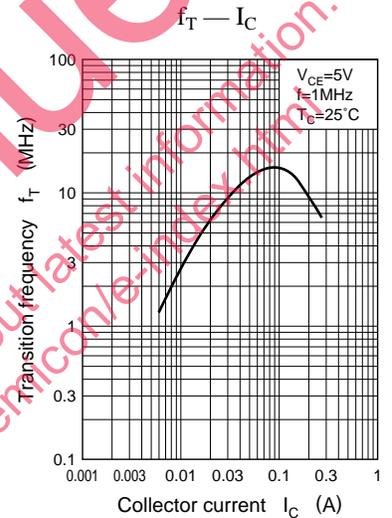
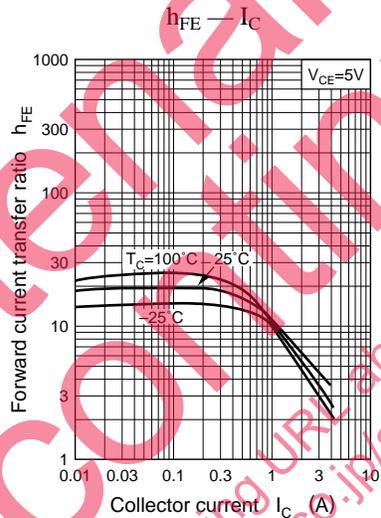
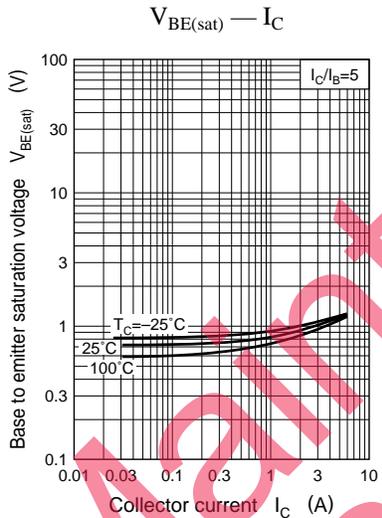
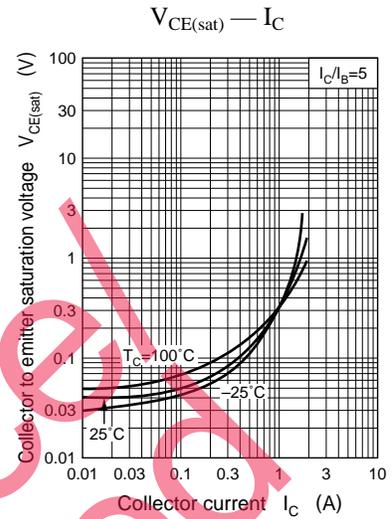
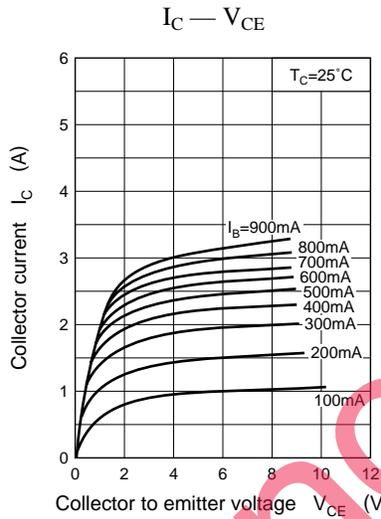
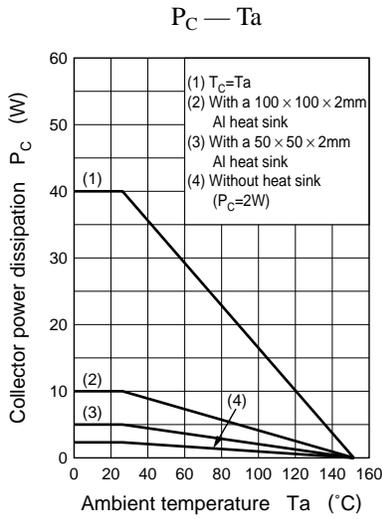
## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Rated	Unit
Collector to base voltage	2SC5037	900	V
	2SC5037A	1000	
Collector to emitter voltage	2SC5037	900	V
	2SC5037A	1000	
Collector to emitter voltage	$V_{CEO}$	800	V
Emitter to base voltage	$V_{EBO}$	7	V
Peak collector current	$I_{CP}$	5	A
Collector current	$I_C$	3	A
Base current	$I_B$	1	A
Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
	$T_a=25^\circ\text{C}$	2	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

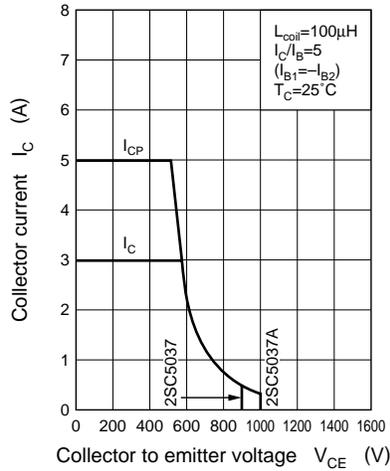


## Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

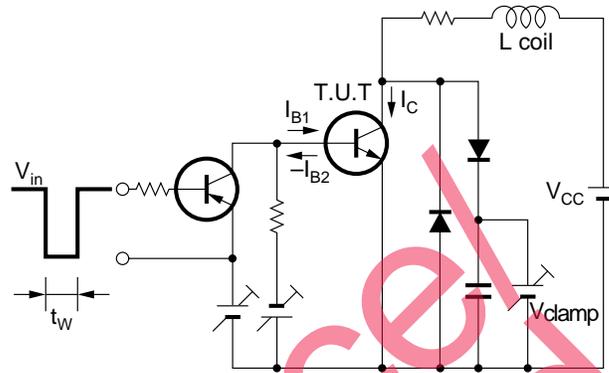
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	2SC5037	$V_{CB} = 900\text{V}, I_E = 0$			50	$\mu\text{A}$
	2SC5037A	$V_{CB} = 1000\text{V}, I_E = 0$			50	
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 7\text{V}, I_C = 0$			50	$\mu\text{A}$
Collector to emitter voltage	$V_{CEO}$	$I_C = 10\text{mA}, I_B = 0$	800			$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 5\text{V}, I_C = 0.1\text{A}$	8			V
	$h_{FE2}$	$V_{CE} = 5\text{V}, I_C = 0.8\text{A}$	6			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.8\text{A}, I_B = 0.16\text{A}$			1.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 0.8\text{A}, I_B = 0.16\text{A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 5\text{V}, I_C = 0.15\text{A}, f = 1\text{MHz}$		10		MHz
Turn-on time	$t_{on}$	$I_C = 0.8\text{A}, I_{B1} = 0.16\text{A}, I_{B2} = -0.32\text{A}, V_{CC} = 250\text{V}$			0.7	$\mu\text{s}$
Storage time	$t_{stg}$				2.5	$\mu\text{s}$
Fall time	$t_f$				0.3	$\mu\text{s}$



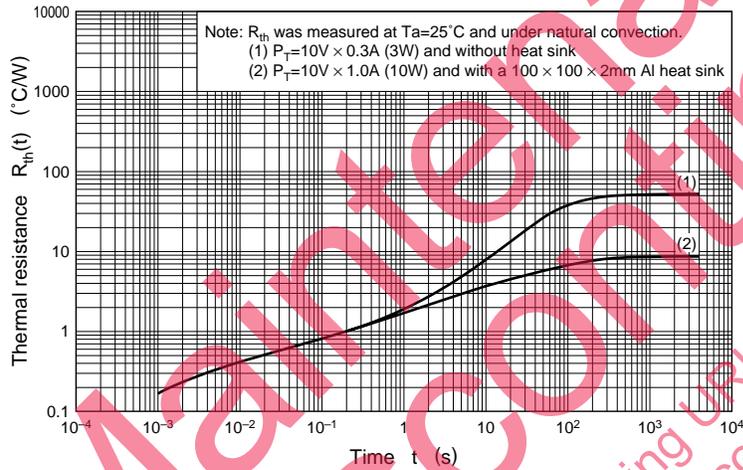
Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit



$R_{th}(t) - t$



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